

## **isc Silicon NPN Power Transistors**

# **KTC2238A**

### **DESCRIPTION**

- · Low Saturation Voltage-
  - :  $V_{CE(sat)}=1.5V(Max)@ (I_C=0.5A, I_B=50mA)$
- · High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 180V(Min)
- · Complement to Type KTA968A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



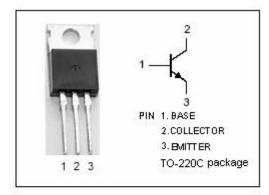
• Designed for high voltage and general purpose applications.

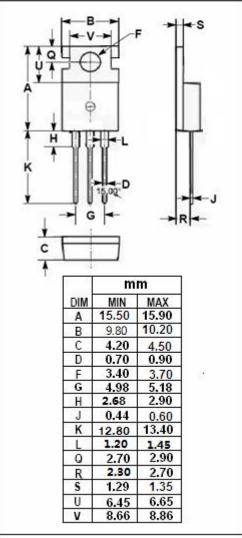
# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	180	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	1.5	А
I <sub>E</sub>	Emitter Current	1.5	А
Pc	Collector Power Dissipation $T_C$ =25 $^{\circ}$ C	25	W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	63	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	180			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	Ic= 0.1mA; I <sub>B</sub> = 0	180			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V			1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 160V; I <sub>E</sub> = 0			1	uA
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1	uA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	70		240	
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V,f <sub>test</sub> = 1MHz		25		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		100		MHz

### ♦ h<sub>FE</sub> Classifications

0	Y	
70-140	120-240	

#### Notice:

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2

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